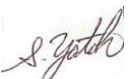
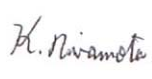


1. TYPE 2SCR523V1
2. STRUCTURE NPN SILICON EPITAXIAL PLANAR TRANSISTOR
3. APPLICATIONS GENERAL PURPOSE SMALL SIGNAL AMPLIFIER
4. ABSOLUTE MAXIMUM RATINGS [Ta=25°C]

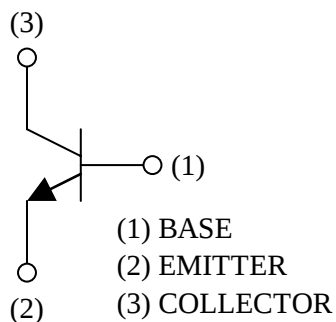
COLLECTOR-BASE VOLTAGE	V_{CBO}	...	50V
COLLECTOR-EMITTER VOLTAGE	V_{CEO}	...	50V
EMITTER-BASE VOLTAGE	V_{EBO}	...	5V
COLLECTOR CURRENT	I_C	...	100mA
	I_{CP}	...	200mA
			$P_W=10\text{ms}$ SINGLE PULSE
POWER DISSIPATION	P_D	...	100mW
			* EACH TERMINAL MOUNTED ON A REFERENCE LAND
JUNCTION TEMPERATURE	T_j	...	150°C
RANGE OF STORAGE TEMPERATURE	T_{stg}	...	-55~150°C

DESIGN	CHECK	APPROVAL	DATE : 23/ JUL / 2012	SPECIFICATION No. TSQ03131-2SCR523V1
			REV. : 0	ROHM Co.,Ltd.

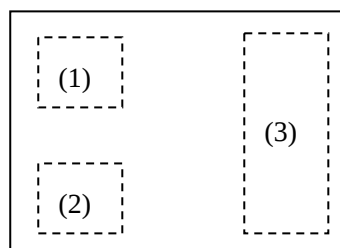
5. ELECTRICAL CHARACTERISTICS [Ta=25°C]

PARAMETER	SYMBOL	CONDITION	MIN.	TYP.	MAX.
COLLECTOR-EMITTER BREAKDOWN VOLTAGE	BV_{CEO}	$I_C=1mA$	50V	-	-
COLLECTOR-BASE BREAKDOWN VOLTAGE	BV_{CBO}	$I_C=50\mu A$	50V	-	-
EMITTER-BASE BREAKDOWN VOLTAGE	BV_{EBO}	$I_E=50\mu A$	5V	-	-
COLLECTOR CUT-OFF CURRENT	I_{CBO}	$V_{CB}=50V$	-	-	0.1 μA
EMITTER CUT-OFF CURRENT	I_{EBO}	$V_{EB}=5V$	-	-	0.1 μA
COLLECTOR-EMITTER SATURATION VOLTAGE	$V_{CE(sat)}$	$I_C=50mA / I_B=5mA$	-	0.10V	0.30V
DC CURRENT GAIN	h_{FE}	$V_{CE}=6V / I_C=1mA$	120	-	560
TRANSITION FREQUENCY	f_T	$V_{CE}=10V / I_E=-10mA$ $f=100MHz$	-	350MHz	-
OUTPUT CAPACITANCE	C_{ob}	$V_{CB}=10V / I_E=0A$ $f=1MHz$	-	1.6pF	-

6. INTERNAL CIRCUIT



TOP VIEW



7. MARKING



“ NB “ MEANS 2SCR523V1

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